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Details

Product Status	Obsolete
Core Processor	HCS12
Core Size	16-Bit
Speed	25MHz
Connectivity	CANbus, I ² C, SCI, SPI
Peripherals	PWM, WDT
Number of I/O	91
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	2.35V ~ 5.25V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LQFP
Supplier Device Package	112-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s12dt256ccpv

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Table 0-3 shows the defects fixed on maskset 2K79X (MC9S12DP256C)

Table 0-3 Defects fixed on Maskset 2K79X

Defect	Headline
MUCts00510	SCI interrupt asserts only if odd number of interrupts active
MUCts00604	Security in Normal Single Chip mode
MUCts00603	Security in Normal Single Chip mode

This document is part of the customer documentation. A complete set of device manuals also includes the HCS12 Core User Guide and all the individual Block User Guides of the implemented modules. In a effort to reduce redundancy all module specific information is located only in the respective Block User Guide. If applicable, special implementation details of the module are given in the block description sections of this document.

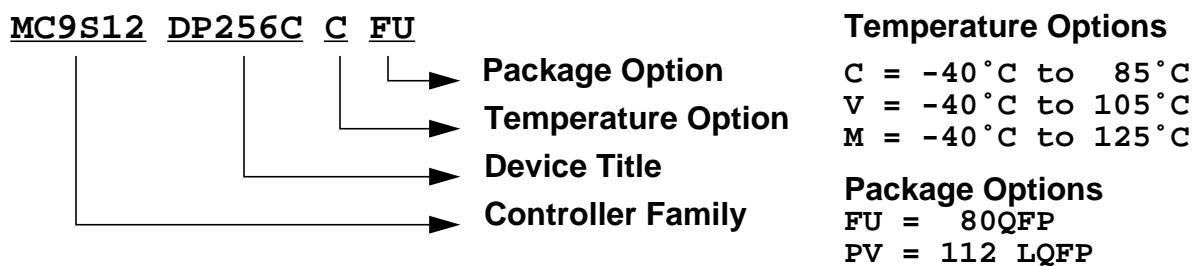


Figure 0-1 Order Part Number Example

See **Table 0-4** for names and versions of the referenced documents throughout the Device User Guide.

Table 0-4 Document References

User Guide	Version	Document Order Number
HCS12 V1.5 Core User Guide	1.2	HCS12COREUG
CRG Block User Guide	V02	S12CRGV2/D
ECT_16B8C Block User Guide	V01	S12ECT16B8CV1/D
ATD_10B8C Block User Guide	V02	S12ATD10B8CV2/D
IIC Block User Guide	V02	S12IICV2/D
SCI Block User Guide	V02	S12SCIV2/D
SPI Block User Guide	V02	S12SPIV2/D
PWM_8B8C Block User Guide	V01	S12PWM8B8CV1/D
FTS256K Block User Guide	V02	S12FTS256KV2/D
EETS4K Block User Guide	V02	S12EETS4KV2/D
BDLC Block User Guide	V01	S12BDLCV1/D
MSCAN Block User Guide	V02	S12MSCANV2/D
VREG Block User Guide	V01	S12VREGV1/D
PIM_9DP256 Block User Guide	V02	S12PIM9DP256V2/D

1.5 Device Memory Map

Table 1-1 and **Figure 1-2** show the device memory map of the MC9S12DP256B after reset. Note that after reset the bottom 1k of the EEPROM (\$0000 - \$03FF) are hidden by the register space.

Table 1-1 Device Memory Map

Address	Module	Size (Bytes)
\$0000 - \$0017	CORE (Ports A, B, E, Modes, Inits, Test)	24
\$0018 - \$0019	Reserved	2
\$001A - \$001B	Device ID register (PARTID)	2
\$001C - \$001F	CORE (MEMSIZ, IRQ, HPPIO)	4
\$0020 - \$0027	Reserved	8
\$0028 - \$002F	CORE (Background Debug Mode)	8
\$0030 - \$0033	CORE (PPAGE, Port K)	4
\$0034 - \$003F	Clock and Reset Generator (PLL, RTI, COP)	12
\$0040 - \$007F	Enhanced Capture Timer 16-bit 8 channels	64
\$0080 - \$009F	Analog to Digital Converter 10-bit 8 channels (ATD0)	32
\$00A0 - \$00C7	Pulse Width Modulator 8-bit 8 channels (PWM)	40
\$00C8 - \$00CF	Serial Communications Interface 0 (SCI0)	8
\$00D0 - \$00D7	Serial Communications Interface 0 (SCI1)	8
\$00D8 - \$00DF	Serial Peripheral Interface (SPI0)	8
\$00E0 - \$00E7	Inter IC Bus	8
\$00E8 - \$00EF	Byte Data Link Controller (BDLC)	8
\$00F0 - \$00F7	Serial Peripheral Interface (SPI1)	8
\$00F8 - \$00FF	Serial Peripheral Interface (SPI2)	8
\$0100- \$010F	Flash Control Register	16
\$0110 - \$011B	EEPROM Control Register	12
\$011C - \$011F	Reserved	4
\$0120 - \$013F	Analog to Digital Converter 10-bit 8 channels (ATD1)	32
\$0140 - \$017F	Motorola Scalable Can (CAN0)	64
\$0180 - \$01BF	Motorola Scalable Can (CAN1)	64
\$01C0 - \$01FF	Motorola Scalable Can (CAN2)	64
\$0200 - \$023F	Motorola Scalable Can (CAN3)	64
\$0240 - \$027F	Port Integration Module (PIM)	64
\$0280 - \$02BF	Motorola Scalable Can (CAN4)	64
\$02C0 - \$03FF	Reserved	320
\$0000 - \$0FFF	EEPROM array	4096
\$1000 - \$3FFF	RAM array	12288
\$4000 - \$7FFF	Fixed Flash EEPROM array incl. 0.5K, 1K, 2K or 4K Protected Sector at start	16384
\$8000 - \$BFFF	Flash EEPROM Page Window	16384

\$0010 - \$0014**MMC map 1 of 4 (Core User Guide)**

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0012	INITEE	Read: EE15	Write: EE14	EE13	EE12	0	0	0	EEON
\$0013		Read: 0	Write: 0	0	0	EXSTR1	EXSTRO	ROMHM	ROMON
\$0014	MTST0	Read: Bit 7	Write: 6	5	4	3	2	1	Bit 0

\$0015 - \$0016**INT map 1 of 2 (Core User Guide)**

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0015	ITCR	Read: 0	Write: 0	0	WRINT	ADR3	ADR2	ADR1	ADR0
\$0016		Read: INTE	Write: INTC	INTA		INT8	INT6	INT4	INT2
	ITEST								INT0

\$0017 - \$0017**MMC map 2 of 4 (Core User Guide)**

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0017	MTST1	Read: Bit 7	Write: 6	5	4	3	2	1	Bit 0

\$0018 - \$001B**Miscellaneous Peripherals (Device User Guide,Table 1-3)**

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0018	Reserved	Read: 0	Write: 0	0	0	0	0	0	0
\$0019		Read: 0	Write: 0	0	0	0	0	0	0
\$001A	PARTIDH	Read: ID15	Write: ID14	ID13	ID12	ID11	ID10	ID9	ID8
\$001B		Read: ID7	Write: ID6	ID5	ID4	ID3	ID2	ID1	ID0

\$001C - \$001D**MMC map 3 of 4 (Core and Device User Guide,Table 1-4)**

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$001C	MEMSIZ0	Read: reg_sw0	Write: 0	eep_sw1	eep_sw0	0	ram_sw2	ram_sw1	ram_sw0
\$001D		Read: rom_sw1	Write: rom_sw0	0	0	0	0	pag_sw1	pag_sw0
	MEMSIZ1								

\$0028 - \$002F**BKP (Core User Guide)**

Address	Name	Read:	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
\$002D	BKP1X	Write:	0	0		BK1V5	BK1V4	BK1V3	BK1V2	BK1V1	BK1V0
\$002E	BKP1H	Read:			Bit 15	14	13	12	11	10	9
\$002F	BKP1L	Write:		Bit 7	6	5	4	3	2	1	Bit 0

\$0030 - \$0031**MMC map 4 of 4 (Core User Guide)**

Address	Name	Read:	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
\$0030	PPAGE	Read:	0	0		PIX5	PIX4	PIX3	PIX2	PIX1	PIX0
\$0031	Reserved	Write:	0	0	0		0	0	0	0	

\$0032 - \$0033**MEBI map 3 of 3 (Core User Guide)**

Address	Name	Read:	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
\$0032	PORTK	Write:	Bit 7	6	5	4	3	2	1	Bit 0	
\$0033	DDRK	Read:	Bit 7	6	5	4	3	2	1	Bit 0	Write:

\$0034 - \$003F**CRG (Clock and Reset Generator)**

Address	Name	Read:	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
\$0034	SYNR	Write:	0	0		SYN5	SYN4	SYN3	SYN2	SYN1	SYN0
\$0035	REFDV	Read:	0	0	0	0		REFDV3	REFDV2	REFDV1	REFDV0
\$0036	CTFLG	Read:	TOUT7	TOUT6	TOUT5	TOUT4	TOUT3	TOUT2	TOUT1	TOUT0	
	TEST ONLY	Write:									
\$0037	CRGFLG	Read:	RTIF	PROF	0	LOCKIF	LOCK	TRACK		SCMIF	SCM
		Write:									
\$0038	CRGINT	Read:	RTIE	0	0	LOCKIE	0	0		SCMIE	0
		Write:									
\$0039	CLKSEL	Read:	PLLSEL	PSTP	SYSWAI	ROAWAI	PLLWAI	CWAI	RTIWAI	COPWAI	
		Write:									
\$003A	PLLCTL	Read:	CME	PLLON	AUTO	ACQ	0		PRE	PCE	SCME
		Write:									
\$003B	RTICTL	Read:	0	RTR6	RTR5	RTR4	RTR3	RTR2	RTR1	RTR0	
		Write:									
\$003C	COPCTL	Read:	WCOP	RSBCK	0	0	0		CR2	CR1	CR0
		Write:									

\$00D8 - \$00DF**SPI0 (Serial Peripheral Interface)**

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$00DC	Reserved	Read: 0	0	0	0	0	0	0	0
		Write: 							
\$00DD	SPI0DR	Read: Bit7	6	5	4	3	2	1	Bit0
		Write: 							
\$00DE	Reserved	Read: 0	0	0	0	0	0	0	0
		Write: 							
\$00DF	Reserved	Read: 0	0	0	0	0	0	0	0
		Write: 							

\$00E0 - \$00E7**IIC (Inter IC Bus)**

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$00E0	IBAD	Read: ADR7	ADR6	ADR5	ADR4	ADR3	ADR2	ADR1	0
		Write: 							
\$00E1	IBFD	Read: IBC7	IBC6	IBC5	IBC4	IBC3	IBC2	IBC1	IBC0
		Write: 							
\$00E2	IBCR	Read: IBEN	IBIE	MS/SL	TX/RX	TXAK	0	0	IBSWAI
		Write: 					RSTA		
\$00E3	IBSR	Read: TCF	IAAS	IBB	IBAL	0	SRW	IBIF	RXAK
		Write: 							
\$00E4	IBDR	Read: D7	D6	D5	D4	D3	D2	D1	D0
		Write: 							
\$00E5	Reserved	Read: 0	0	0	0	0	0	0	0
		Write: 							
\$00E6	Reserved	Read: 0	0	0	0	0	0	0	0
		Write: 							
\$00E7	Reserved	Read: 0	0	0	0	0	0	0	0
		Write: 							

\$00E8 - \$00EF**BDLC (Bytelevel Data Link Controller J1850)**

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$00E8	DLCBCR1	Read: IMSG	CLKS	0	0	0	0	IE	WCM
		Write: 							
\$00E9	DLCBSVR	Read: 0	0	I3	I2	I1	I0	0	0
		Write: 							
\$00EA	DLCBCR2	Read: SMRST	DLOOP	RX4XE	NBFS	TEOD	TSIFR	TMIFR1	TMIFR0
		Write: 							
\$00EB	DLCBDR	Read: D7	D6	D5	D4	D3	D2	D1	D0
		Write: 							
\$00EC	DLCBARD	Read: 0	RXPOL	0	0	BO3	BO2	BO1	BO0
		Write: 							
\$00ED	DLCBRSR	Read: 0	0	R5	R4	R3	R2	R1	R0
		Write: 							
\$00EE	DLCSCR	Read: 0	0	0	BDLCE	0	0	0	0
		Write: 							
\$00EF	DLCBSTAT	Read: 0	0	0	0	0	0	0	IDLE
		Write: 							

\$0110 - \$011B

EEPROM Control Register (eets4k)

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0119	EADDRLO	Read: Write:	Bit 7	6	5	4	3	2	1 Bit 0
\$011A	EDATAHI	Read: Write:	Bit 15	14	13	12	11	10	9 Bit 8
\$011B	EDATALO	Read: Write:	Bit 7	6	5	4	3	2	1 Bit 0

\$011C - \$011F

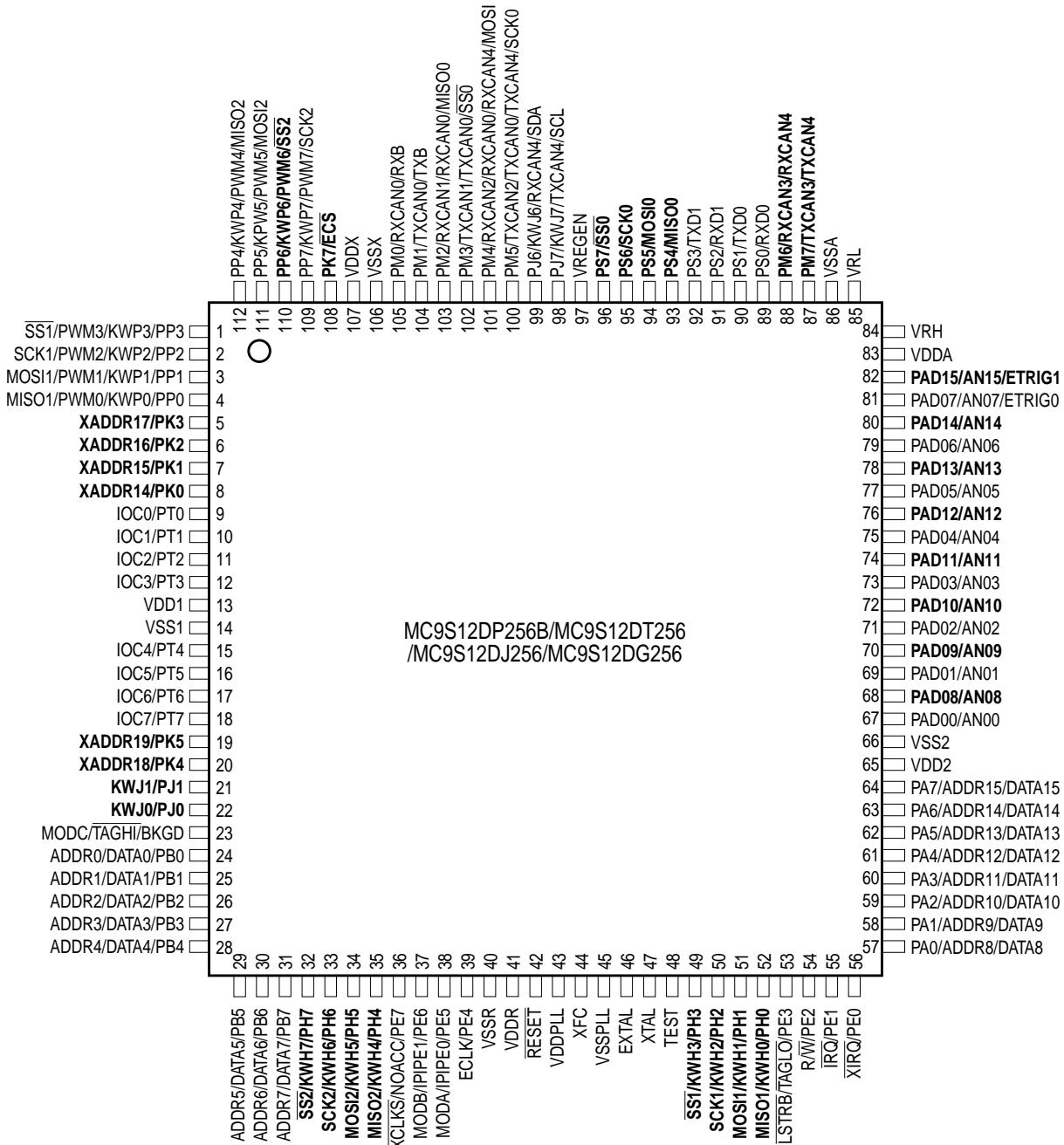
Reserved for RAM Control Register

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$011C	Reserved	Read: Write:	0	0	0	0	0	0	0
\$011D	Reserved	Read: Write:	0	0	0	0	0	0	0
\$011E	Reserved	Read: Write:	0	0	0	0	0	0	0
\$011F	Reserved	Read: Write:	0	0	0	0	0	0	0

\$0120 - \$013F

ATD1 (Analog to Digital Converter 10 Bit 8 Channel)

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0120	ATD1CTL0	Read: Write:	0	0	0	0	0	0	0
\$0121	ATD1CTL1	Read: Write:	0	0	0	0	0	0	0
\$0122	ATD1CTL2	Read: Write:	ADPU	AFFC	AWAI	ETRIGLE	ETRIGP	ETRIG	ASCIE
\$0123	ATD1CTL3	Read: Write:	0	S8C	S4C	S2C	S1C	FIFO	FRZ1
\$0124	ATD1CTL4	Read: Write:	SRES8	SMP1	SMP0	PRS4	PRS3	PRS2	PRS1
\$0125	ATD1CTL5	Read: Write:	DJM	DSGN	SCAN	MULT	0	CC	CB
\$0126	ATD1STAT0	Read: Write:	SCF	0	ETORF	FIFOR	0	CC2	CC1
\$0127	Reserved	Read: Write:	0	0	0	0	0	0	0
\$0128	ATD1TEST0	Read: Write:	0	0	0	0	0	0	0
\$0129	ATD1TEST1	Read: Write:	0	0	0	0	0	0	SC
\$012A	Reserved	Read: Write:	0	0	0	0	0	0	0
\$012B	ATD1STAT1	Read: Write:	CCF7	CCF6	CCF5	CCF4	CCF3	CCF2	CCF1
\$012C	Reserved	Read: Write:	0	0	0	0	0	0	0



Signals shown in **Bold** are not available on the 80 Pin Package

Figure 2-1 Pin Assignments in 112-pin LQFP

Section 3 System Clock Description

3.1 Overview

The Clock and Reset Generator provides the internal clock signals for the core and all peripheral modules. **Figure 3-1** shows the clock connections from the CRG to all modules.

Consult the CRG Block User Guide for details on clock generation.

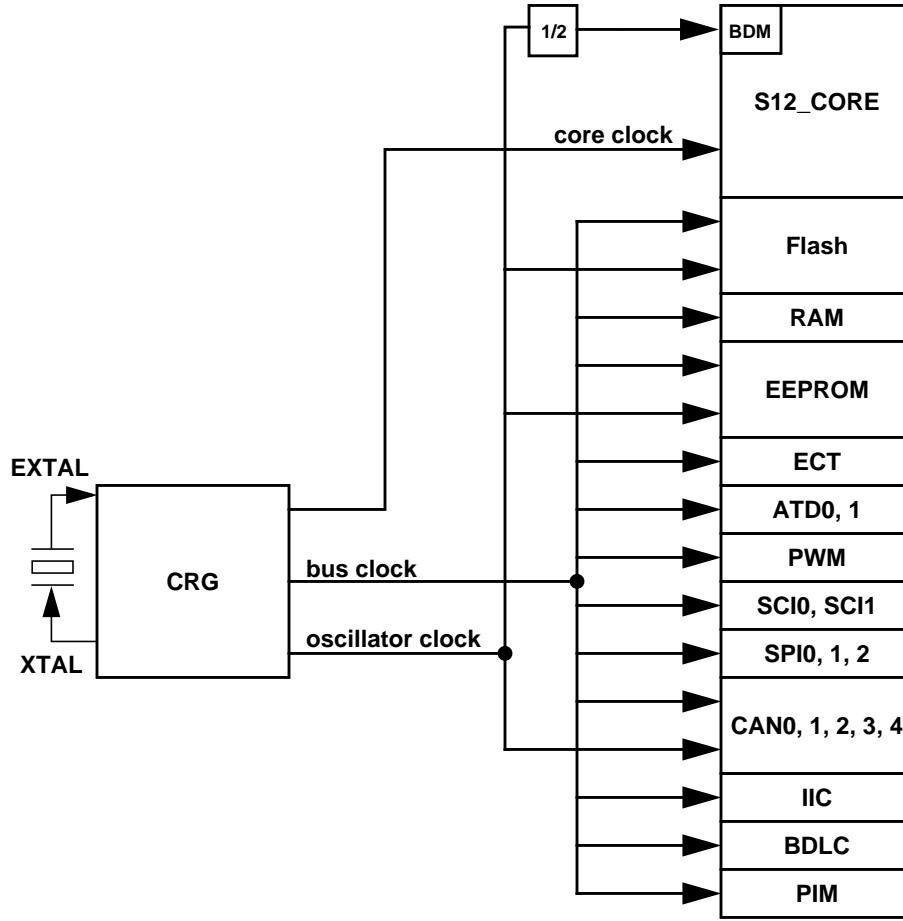


Figure 3-1 Clock Connections

Section 6 HCS12 Core Block Description

Consult the HCS12 Core User Guide for information about the HCS12 core modules, i.e. central processing unit (CPU), interrupt module (INT), module mapping control module (MMC), multiplexed external bus interface (MEBI), breakpoint module (BKP) and background debug mode module (BDM).

Table 6-1 Configuration of HCS12 Core

Name	Description	MC9S12DP256B Configuration
PUCR_RESET	PUCR reset state	\$90
NUM_INT	Interrupt Request Bus Width	56
INITEE_RST	INITEE reset state	\$01
INITEE_WOK	INITEE Write anytime in normal mode	INITEE register is writeable once in normal modes
PPAGE_SMOD_ONLY	PPAGE Write only in special mode	PPAGE register is writable in all modes,reset state of the PPAGE register is \$00

Section 7 Clock and Reset Generator (CRG) Block Description

Consult the CRG Block User Guide for information about the Clock and Reset Generator module.

7.1 Device-specific information

7.1.1 XCLKS

The XCLKS input signal is active low (see 2.3.13 PE7 / NOACC / XCLKS — Port E I/O Pin 7).

Section 8 Enhanced Capture Timer (ECT) Block Description

Consult the ECT_16B8C Block User Guide for information about the Enhanced Capture Timer module.

Section 9 Analog to Digital Converter (ATD) Block Description

There are two Analog to Digital Converters (ATD1 and ATD0) implemented on the MC9S12DP256B. Consult the ATD_10B8C Block User Guide for information about each Analog to Digital Converter module.

Section 10 Inter-IC Bus (IIC) Block Description

Consult the IIC Block User Guide for information about the Inter-IC Bus module.

Section 11 Serial Communications Interface (SCI) Block Description

There are two Serial Communications Interfaces (SCI1 and SCI0) implemented on the MC9S12DP256B device. Consult the SCI Block User Guide for information about each Serial Communications Interface module.

Section 12 Serial Peripheral Interface (SPI) Block Description

There are three Serial Peripheral Interfaces(SPI2, SPI1 and SPI0) implemented on MC9S12DP256B. Consult the SPI Block User Guide for information about each Serial Peripheral Interface module.

Section 13 J1850 (BDLC) Block Description

Consult the BDLC Block User Guide for information about the J1850 module.

Section 14 Pulse Width Modulator (PWM) Block Description

Consult the PWM_8B8C Block User Guide for information about the Pulse Width Modulator module.

Section 15 Flash EEPROM 256K Block Description

Consult the FTS256K Block User Guide for information about the flash module.

Section 16 EEPROM 4K Block Description

Consult the EETS4K Block User Guide for information about the EEPROM module.

Section 17 RAM Block Description

A.1.7 Operating Conditions

This chapter describes the operating conditions of the device. Unless otherwise noted those conditions apply to all the following data.

NOTE: Please refer to the temperature rating of the device (C , V , M) with regards to the ambient temperature T_A and the junction temperature T_J . For power dissipation calculations refer to **Section A.1.8 Power Dissipation and Thermal Characteristics**.

Table A-4 Operating Conditions

Rating	Symbol	Min	Typ	Max	Unit
I/O, Regulator and Analog Supply Voltage	V_{DD5}	4.5	5	5.25	V
Digital Logic Supply Voltage ¹	V_{DD}	2.35	2.5	2.75	V
PLL Supply Voltage ²	V_{DDPLL}	2.35	2.5	2.75	V
Voltage Difference VDDX to VDDR and VDDA	Δ_{VDDX}	-0.1	0	0.1	V
Voltage Difference VSSX to VSSR and VSSA	Δ_{VSSX}	-0.1	0	0.1	V
Oscillator	f_{osc}	0.5	-	16	MHz
Bus Frequency	f_{bus}	0.5	-	25	MHz
MC9S12DP256BC					
Operating Junction Temperature Range	T_J	-40	-	100	°C
Operating Ambient Temperature Range ²	T_A	-40	27	85	°C
MC9S12DP256BV					
Operating Junction Temperature Range	T_J	-40	-	120	°C
Operating Ambient Temperature Range ²	T_A	-40	27	105	°C
MC9S12DP256BM					
Operating Junction Temperature Range	T_J	-40	-	140	°C
Operating Ambient Temperature Range ²	T_A	-40	27	125	°C

NOTES:

1. The device contains an internal voltage regulator to generate the logic and PLL supply out of the I/O supply. The absolute maximum ratings apply when this regulator is disabled and the device is powered from an external source.
2. Please refer to **Section A.1.8 Power Dissipation and Thermal Characteristics** for more details about the relation between ambient temperature T_A and device junction temperature T_J .

A.1.8 Power Dissipation and Thermal Characteristics

Power dissipation and thermal characteristics are closely related. The user must assure that the maximum operating junction temperature is not exceeded. The average chip-junction temperature (T_J) in °C can be obtained from:

A.3.1.3 Sector Erase

Erasing a 512 byte Flash sector or a 4 byte EEPROM sector takes:

$$t_{era} \approx 4000 \cdot \frac{1}{f_{NVMOP}}$$

The setup time can be ignored for this operation.

A.3.1.4 Mass Erase

Erasing a NVM block takes:

$$t_{mass} \approx 20000 \cdot \frac{1}{f_{NVMOP}}$$

The setup time can be ignored for this operation.

A.3.1.5 Blank Check

The time it takes to perform a blank check on the Flash or EEPROM is dependant on the location of the first non-blank word starting at relative address zero. It takes one bus cycle per word to verify plus a setup of the command.

$$t_{check} \approx \text{location} \cdot t_{cyc} + 10 \cdot t_{cyc}$$

Table A-11 NVM Timing Characteristics

Conditions are shown in Table A-4 unless otherwise noted							
Num	C	Rating	Symbol	Min	Typ	Max	Unit
1	D	External Oscillator Clock	f_{NVMOsc}	0.5		50 ¹	MHz
2	D	Bus frequency for Programming or Erase Operations	f_{NVMbus}	1			MHz
3	D	Operating Frequency	f_{NVMOP}	150		200	kHz
4	P	Single Word Programming Time	t_{swpgm}	46 ²		74.5 ³	μs
5	D	Flash Burst Programming consecutive word ⁴	t_{bwpgm}	20.4 ²		31 ³	μs
6	D	Flash Burst Programming Time for 32 Words ⁴	t_{brpgm}	678.4 ²		1035.5 ³	μs
7	P	Sector Erase Time	t_{era}	20 ⁵		26.7 ³	ms
8	P	Mass Erase Time	t_{mass}	100 ⁵		133 ³	ms
9	D	Blank Check Time Flash per block	t_{check}	11 ⁶		32778 ⁷	t_{cyc}
10	D	Blank Check Time EEPROM per block	t_{check}	11 ⁶		2058 ⁷	t_{cyc}

NOTES:

1. Restrictions for oscillator in crystal mode apply!
2. Minimum Programming times are achieved under maximum NVM operating frequency f_{NVMOP} and maximum bus frequency f_{bus} .

3. Maximum Erase and Programming times are achieved under particular combinations of f_{NVMOP} and bus frequency f_{bus} . Refer to formulae in Sections **A.3.1.1 - A.3.1.4** for guidance.
4. First Programming operations are not applicable to EEPROM
5. Minimum Erase times are achieved under maximum NVM operating frequency f_{NVMOP} .
6. Minimum time, if first word in the array is not blank
7. Maximum time to complete check on an erased block

A.3.2 NVM Reliability

The reliability of the NVM blocks is guaranteed by stress test during qualification, constant process monitors and burn-in to screen early life failures.

The failure rates for data retention and program/erase cycling are specified at the operating conditions noted.

The program/erase cycle count on the sector is incremented every time a sector or mass erase event is executed.

NOTE: All values shown in **Table A-12** are target values and subject to further extensive characterization.

Table A-12 NVM Reliability Characteristics

Conditions are shown in Table A-4 unless otherwise noted						
Num	C	Rating	Cycles	Data Retention Lifetime	Unit	
1	C	Flash/EEPROM (-40C to + 125C)	10	15	Years	
2	C	EEPROM (-40C to + 125C)	10,000	5	Years	

NOTE: Flash cycling performance is 10 cycles at -40C to + 125C. Data retention is specified for 15 years.

NOTE: EEPROM cycling performance is 10K cycles at -40C to +125C. Data retention is specified for 5 years on words after cycling 10K times. However if only 10 cycles are executed on a word the data retention is specified for 15 years.

A.4 Voltage Regulator

The on-chip voltage regulator is intended to supply the internal logic and oscillator circuits. No external DC load is allowed.

Table A-13 Voltage Regulator Recommended Load Capacitances

Rating	Symbol	Min	Typ	Max	Unit
Load Capacitance on VDD1, 2	C_{LVDD}		220		nF
Load Capacitance on VDDPLL	$C_{LVDDfcPLL}$		220		nF

The loop bandwidth f_C should be chosen to fulfill the Gardner's stability criteria by at least a factor of 10, typical values are 50. $\zeta = 0.9$ ensures a good transient response.

$$f_C < \frac{2 \cdot \zeta \cdot f_{\text{ref}}}{\pi \cdot (\zeta + \sqrt{1 + \zeta^2})} \cdot \frac{1}{50} \rightarrow f_C < \frac{f_{\text{ref}}}{4 \cdot 50}; (\zeta = 0.9)$$

And finally the frequency relationship is defined as

$$n = \frac{f_{\text{VCO}}}{f_{\text{ref}}} = 2 \cdot (\text{synr} + 1)$$

With the above inputs the resistance can be calculated as:

$$R = \frac{2 \cdot \pi \cdot n \cdot f_C}{K_\Phi}$$

The capacitance C_s can now be calculated as:

$$C_s = \frac{2 \cdot \zeta^2}{\pi \cdot f_C \cdot R} \approx \frac{0.516}{f_C \cdot R}; (\zeta = 0.9)$$

The capacitance C_p should be chosen in the range of:

$$C_s/20 \leq C_p \leq C_s/10$$

The stabilization delays shown in **Table A-16** are dependant on PLL operational settings and external component selection (e.g. crystal, XFC filter).

A.5.3.2 Jitter Information

The basic functionality of the PLL is shown in **Figure A-2**. With each transition of the clock f_{cmp} , the deviation from the reference clock f_{ref} is measured and input voltage to the VCO is adjusted accordingly. The adjustment is done continuously with no abrupt changes in the clock output frequency. Noise, voltage, temperature and other factors cause slight variations in the control loop resulting in a clock jitter. This jitter affects the real minimum and maximum clock periods as illustrated in **Figure A-3**.

This is very important to notice with respect to timers, serial modules where a pre-scaler will eliminate the effect of the jitter to a large extent.

Table A-16 PLL Characteristics

Conditions are shown in Table A-4 unless otherwise noted							
Num	C	Rating	Symbol	Min	Typ	Max	Unit
1	P	Self Clock Mode frequency	f_{SCM}	1		5.5	MHz
2	D	VCO locking range	f_{VCO}	8		50	MHz
3	D	Lock Detector transition from Acquisition to Tracking mode	$ \Delta_{trk} $	3		4	% ¹
4	D	Lock Detection	$ \Delta_{Lock} $	0		1.5	% ¹
5	D	Un-Lock Detection	$ \Delta_{unl} $	0.5		2.5	% ¹
6	D	Lock Detector transition from Tracking to Acquisition mode	$ \Delta_{untl} $	6		8	% ¹
7	C	PLLON Total Stabilization delay (Auto Mode) ²	t_{stab}		0.5		ms
8	D	PLLON Acquisition mode stabilization delay ²	t_{acq}		0.3		ms
9	D	PLLON Tracking mode stabilization delay ²	t_{al}		0.2		ms
10	D	Fitting parameter VCO loop gain	K_1		-120		MHz/V
11	D	Fitting parameter VCO loop frequency	f_1		75		MHz
12	D	Charge pump current acquisition mode	$ i_{ch} $		38.5		μA
13	D	Charge pump current tracking mode	$ i_{ch} $		3.5		μA
14	C	Jitter fit parameter 1 ²	j_1			1.1	%
15	C	Jitter fit parameter 2 ²	j_2			0.13	%

NOTES:

1. % deviation from target frequency

2. $f_{REF} = 4\text{MHz}$, $f_{BUS} = 25\text{MHz}$ equivalent $f_{VCO} = 50\text{MHz}$: REFDV = #\$03, SYNR = #\$018, $C_s = 4.7\text{nF}$, $C_p = 470\text{pF}$, $R_s = 10\text{k}\Omega$.